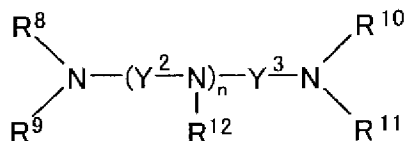
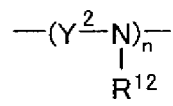


Amendments To The Claims:

1. (Currently amended) A polishing composition for use in polishing a silicon wafer, the polishing composition consisting of ~~comprising~~ a chelating agent, an alkali compound, silicon dioxide and water, wherein the chelating agent is an acid represented by the following chemical formula:



or a salt thereof, and wherein in the chemical formula, each of Y² and Y³ represents an alkylene group, n is an integer of 0 to 4,



is a bond when n is zero, each of 4+n substituents represented by R⁸ to R¹² is an alkyl group and at least four of the alkyl groups have a phosphonic acid group.

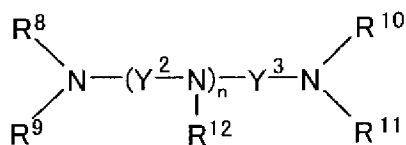
2. (Previously presented) The polishing composition according to claim 1, wherein the alkylene group is a lower alkylene group having 1 to 4 carbon atoms.
3. (Previously presented) The polishing composition according to claim 1, wherein the alkyl group is a lower alkyl group having 1 to 4 carbon atoms.
4. (Previously presented) The polishing composition according to claim 1, wherein all the alkyl groups have a phosphonic acid group.
5. (Previously presented) The polishing composition according to claim 1, wherein the chelating agent contains at least one compound selected from ethylenediaminetetraethylenephosphonic acid, ethylenediaminetetramethylenephosphonic acid, diethylenetriaminepentaethylenephosphonic acid, diethylenetriaminepentamethylenephosphonic acid, triethylenetetraminehexaethylenephosphonic acid, triethylenetetraminehexamethylenephosphonic acid, propanediaminetetraethylenephosphonic acid and propanediaminetetramethylenephosphonic acid, and ammonium salts, potassium salts,

sodium salts and lithium salts of these acids.

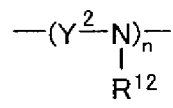
6. (Previously presented) The polishing composition according to claim 1, wherein the polishing composition has a pH of from 8 to 12.

7. (Previously presented) The polishing composition according to claim 1, wherein n in the chemical formula is an integer of 0 to 2.

8. (Currently amended) A process for polishing a silicon wafer, the process comprising:
preparing a polishing composition and
polishing the surface of the silicon wafer by using the polishing composition,
wherein the polishing composition consists of ~~includes~~ a chelating agent, an alkali compound, silicon dioxide and water, wherein the chelating agent is an acid represented by the following chemical formula:



or a salt thereof, and wherein in the chemical formula, each of Y² and Y³ represents an alkylene group, n is an integer of 0 to 4,



is a bond when n is zero, each of 4+n substituents represented by R⁸ to R¹² is an alkyl group and at least four of the alkyl groups have a phosphonic acid group.

9. (Canceled)

10. (Currently amended) ~~The rinsing composition according to claim 9~~ The process according to claim 16, wherein the alkylene group of the chelating agent in the rinsing composition is a lower alkylene group having 1 to 4 carbon atoms.

11. (Currently amended) ~~The rinsing composition according to claim 9~~ The process according to claim 16, wherein the alkyl group of the chelating agent in the rinsing composition is a lower alkyl group having 1 to 4 carbon atoms.

12. (Currently amended) ~~The rinsing composition according to claim 9~~ The process according to claim 16, wherein all the alkyl groups of the chelating agent in the rinsing composition have a phosphonic acid group.

13. (Currently amended) ~~The rinsing composition according to claim 9~~ The process according to claim 16, wherein the chelating agent in the rinsing composition contains at least one compound selected from ethylenediaminetetraethylenephosphonic acid, ethylenediaminetetramethylenephosphonic acid, diethylenetriaminepentaethylenephosphonic acid, diethylenetriaminepentamethylenephosphonic acid, triethylenetetraminehexaethylenephosphonic acid, triethylenetetraminehexamethylenephosphonic acid, propanediaminetetraethylenephosphonic acid and propanediaminetetramethylenephosphonic acid, and ammonium salts, potassium salts, sodium salts and lithium salts of these acids.

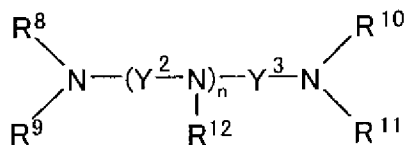
14. (Currently amended) ~~The rinsing composition according to claim 9~~ The process according to claim 16, wherein the rinsing composition has a pH of from 8 to 12.

15. (Currently amended) ~~The rinsing composition according to claim 9~~ The process according to claim 16, wherein n in the chemical formula of the chelating agent in the rinsing composition is an integer of 0 to 2.

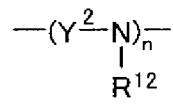
16. (Currently amended) ~~A process for rinsing a silicon wafer, the~~ The process according to claim 8, further comprising:

preparing a rinsing composition and
rinsing the surface of the silicon wafer by using the rinsing composition after polishing the surface of the silicon wafer by using the polishing composition,

wherein the rinsing composition includes a chelating agent, an alkali compound and water, wherein the chelating agent is an acid represented by the following chemical formula:

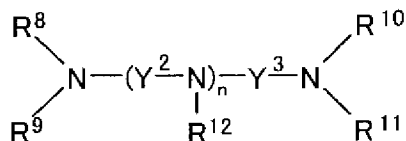


or a salt thereof, and wherein in the chemical formula, each of Y² and Y³ represents an alkylene group, n is an integer of 0 to 4,

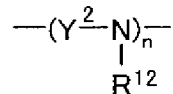


is a bond when n is zero, each of 4+n substituents represented by R⁸ to R¹² is an alkyl group and at least four of the alkyl groups have a phosphonic acid group.

17. (New) A polishing composition for use in polishing a silicon wafer, the polishing composition consisting of a chelating agent, an alkali compound, silicon dioxide, water and at least one selected from the group consisting of a surfactant and an antiseptic agent, wherein the chelating agent is an acid represented by the following chemical formula:



or a salt thereof, and wherein in the chemical formula, each of Y² and Y³ represents an alkylene group, n is an integer of 0 to 4,



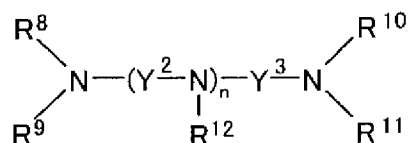
is a bond when n is zero, each of 4+n substituents represented by R⁸ to R¹² is an alkyl group and at least four of the alkyl groups have a phosphonic acid group.

18. (New) A process for polishing a silicon wafer, the process comprising:

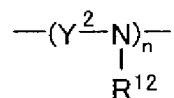
preparing a polishing composition and

polishing the surface of the silicon wafer by using the polishing composition,

wherein the polishing composition consists of a chelating agent, an alkali compound, silicon dioxide, water and at least one selected from the group consisting of a surfactant and an antiseptic agent, wherein the chelating agent is an acid represented by the following chemical formula:



or a salt thereof, and wherein in the chemical formula, each of Y² and Y³ represents an alkylene group, n is an integer of 0 to 4,



is a bond when n is zero, each of 4+n substituents represented by R⁸ to R¹² is an alkyl group and at least four of the alkyl groups have a phosphonic acid group.